

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. SEPP9.001APC	INTERNATIONAL APPLICATION NO. PCT/FI99/00741
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Leskela et al.	
		INTERNATIONAL FILING DATE September 13, 1999	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
<i>MAA</i>	4,927,670	5/22/90	Erbil				
<i>MAA</i>	4,058,430	11/15/77	Suntola et al.				

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
MAA		A1 0 344 352	12/6/89	EPO			X	
MAA		A1 2 626 110	7/21/89	FR				X
MAA		PCT/FI 99/00741	12/2/1999	International Search Report			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>MAA</i>	<i>Materials</i> Science and Engineering, Volume B41, 1996, Lauri Niinisto et al, "Synthesis of oxide thin films and overlayers by atomica layer epitaxy for advanced applications" page 23-29.

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EXAMINER <i>Matthew Anderson</i>	DATE CONSIDERED <i>9/11/02</i>
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SEPP9.001APCAPPLICATION NO.
09/787,062INFORMATION DISCLOSURE STATEMENT
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Leskela et al.FILING DATE
March 12, 2001GROUP
UnknownEXAMINER
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OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

7	Niinistö et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," <u>Materials Science & Engineering</u> , Vol. B41, pp. 23-29 (1996).
8	Ritala et al., "Growth of titanium dioxide thin films by atomic layer epitaxy," <u>Thin Solid Films</u> , Vol. 225, pp. 288-295 (1993).
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13	<u>Advances in Organometallic Chemistry</u> , Ed. Stone and West, Vol. 40, Academic Press (1996).
14	Suntola, "Atomic layer epitaxy," <u>Thin Solid Films</u> , Vol. 216, pp. 84-89 (1992).
15	Wojtczak et al., "A Review of Group 2 (Ca, Sr, Ba) Metal-Organic Compounds as Precursors for Chemical Vapor Deposition," <u>Advances in Organometallic Chemistry</u> , Vol. 40, pp. 215-340 Academic Press (1996).

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